L Number	Hits	Search Text	DB	Time stamp
Number	3203	438/22\$1.ccls. or 438/518.ccls. or	USPAT;	2004/07/12
	3203	438/519.ccls. or 438/527.ccls.	US-PGPUB; EPO; JPO;	10:56
-	18	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high	DERWENT USPAT; US-PGPUB;	2003/12/15 17:46
		with voltage with (n adj well)) and (low with voltage with (p adj well))	EPO; JPO; DERWENT	
-	1	<pre>(sixth adj mask\$3) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:21
-	70	(438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 18:40
_	68	((438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.) and (high with voltage with well) and (low with voltage with well) and (@ad<20020222 or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:47
-	324	<pre>@rlad<20020222) (high with voltage with well) and (first with low with voltage with well) and</pre>	USPAT; US-PGPUB;	2003/12/15 19:55
-	39	(second with low with voltage with well) ((high with voltage with well) and (first with low with voltage with well) and	EPO; JPO; DERWENT USPAT; US-PGPUB;	2003/12/15 19:29
		<pre>(second with low with voltage with well)) and (implant\$5 with (p adj (body or region or well)))</pre>	EPO; JPO; DERWENT	
_	0	20030162375.URPN.	USPAT	2003/12/15
_	44	257/548.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15
_	35	<pre>((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with p with high with voltage)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
_	7	((first with mask\$3) same (implant\$5 with high with voltage with well)) and ((second with mask\$3) same (first with low with voltage with well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:57
-	2579	high with voltage with well with (implant\$5 or form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:22
-	201	low with voltage with well with (implant\$5 or form\$3) with first	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	196	low with voltage with well with (implant\$5 or form\$3) with second	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	114	(high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
-	3208	438/22\$1.ccls. or 438/518.ccls. or 438/519.ccls. or 438/527.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:24

_	11	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (438/22\$1.ccls. or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:52
		438/518.ccls. or 438/519.ccls. or 438/527.ccls.)		
-	6	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:42
-	7	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
-	8	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with mask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
-	144	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
-	131	(((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
-	1	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with photoresist with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:53
-	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:55
-	5	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:58
-	21	<pre>((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:59
-	1	<pre>((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode and mems</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16
-	3	<pre>((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and mems</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:10
-	21	(high with voltage with well) and (low with voltage with well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:35
_	1	(high adj voltage adj well) and (low adj voltage adj well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:11

	T		T	1 0000 /4 2 /2 2
_	2	cmos same dmos same mems	USPAT;	2003/12/16
			US-PGPUB;	21:04
			EPO; JPO;	
			DERWENT	
_	10	cmos and dmos and mems	USPAT;	2003/12/16
			US-PGPUB;	21:05
	<u> </u>		EPO; JPO;	
			DERWENT	
_	2420	mem same (accelerometer or sensor)	USPAT;	2003/12/16
		mom bamo (acceptamental or beinger)	US-PGPUB;	21:03
			EPO; JPO;	21.03
	•		DERWENT	
	2420	mems same (accelerometer or sensor)	USPAT;	2003/12/16
_	2420	mems same (accelerometer of sensor)		
	1		US-PGPUB;	21:03
			EPO; JPO;	
			DERWENT	
-	1862	mems with (accelerometer or sensor)	USPAT;	2003/12/16
			US-PGPUB;	21:03
			EPO; JPO;	
			DERWENT	
-	509	mems with accelerometer	USPAT;	2003/12/16
			US-PGPUB;	21:03
			EPO; JPO;	
			DERWENT	
l _	2	cmos same dmos same photodiode	USPAT;	2003/12/16
[-	2	Curos same muos same buorontone	US-PGPUB;	21:18
				21.10
	1		EPO; JPO;] 1
			DERWENT	0000/10/16
-	16	cmos and dmos and photodiode	USPAT;	2003/12/16
1			US-PGPUB;	21:05
			EPO; JPO;	
			DERWENT	
-	31	cmos same dmos same soi	USPAT;	2003/12/16
			US-PGPUB;	21:18
			EPO; JPO;	
			DERWENT	
_	2	5578506.pn.	USPAT;	2003/12/16
	-	, 00,000,p	US-PGPUB;	21:30
1	1		EPO; JPO;	
1			DERWENT	1
		5601761 nn	USPAT;	2003/12/16
-	2	5681761.pn.	US-PGPUB;	21:30
				21.30
			EPO; JPO;	
			DERWENT	2002/12/16
-	113	(high with voltage with well) and (low	USPAT;	2003/12/16
		with voltage with well) and photodiode	US-PGPUB;	21:36
			EPO; JPO;	
			DERWENT	
-	104	((high with voltage with well) and (low	USPAT;	2003/12/16
		with voltage with well) and photodiode)	US-PGPUB;	21:47
		and @ad<20020222	EPO; JPO;	
			DERWENT	
_	1	(high adj voltage adj well) and (low adj	USPAT;	2003/12/16
		voltage adj well) and photodiode	US-PGPUB;	21:37
1		l torrage adj werr, and photoarous	EPO; JPO;	
			DERWENT	
	71000			2002/12/16
-	71986	photodiode	USPAT;	2003/12/16
			US-PGPUB;	21:48
1			EPO; JPO;	
1			DERWENT	1
-	67	photodiode and dmos	USPAT;	2003/12/16
			US-PGPUB;	21:48
			EPO; JPO;	
			DERWENT	
_	35	(implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) and (implant\$5 with low with	US-PGPUB;	14:03
		voltage with well) and (first adj mask)	EPO; JPO;	
	1	and (second adj mask)	DERWENT	
1 .	1	land (second add mask)	L DELYMENT	

		<u> </u>		
-	28	(implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) and (implant\$5 with low with	US-PGPUB;	14:21
	1	voltage with well) and (first adj mask)	EPO; JPO;	
		and (second adj mask) and (@ad<20020222	DERWENT	
	_	or @rlad<20020222)		
-	0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first adj protective)) and	US-PGPUB;	14:23
		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second adj protective)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		
-	0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) same (first adj oxide)) and	US-PGPUB;	14:23
		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second adj oxide)) and	DERWENT	
		(@ad<20020222 or @rlad<20020222)		0004/05/00
-	0	((implant\$5 with high with voltage with	USPAT;	2004/06/29
	İ	well) same (first with protective)) and	US-PGPUB;	15:48
		((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second with protective)) and	DERWENT	İ
		(@ad<20020222 or @rlad<20020222)		0004/06/00
-	8	((implant\$5 with high with voltage with	USPAT;	2004/06/29
	ļ	well) same (first with oxide)) and	US-PGPUB;	14:41
	1	((implant\$5 with low with voltage with	EPO; JPO;	
		well) same(second with oxide)) and	DERWENT	
	1.50	(@ad<20020222 or @rlad<20020222)	IICDAM.	2004/06/29
_	152	((implant\$5 with high with voltage with	USPAT;	
		well) same (implant\$5 with low with	US-PGPUB;	14:28
		voltage with well)) and (@ad<20020222 or @rlad<20020222)	EPO; JPO; DERWENT	·
_	77	(((implant\$5 with high with voltage with	USPAT;	2004/06/29
	1 ''	well) same (implant\$5 with low with	US-PGPUB;	14:28
		voltage with well)) and (@ad<20020222 or	EPO; JPO;	
		@rlad<20020222)) and 438/\$3.ccls.	DERWENT	
-	7	(implant\$5 with high with voltage with	USPAT;	2004/06/29
	· ·	well with first with mask) and (implant\$5	US-PGPUB;	14:42
		with low with voltage with well with	EPO; JPO;	
		second with mask) and (@ad<20020222 or	DERWENT	
		@rlad<20020222)		
_	3	((high with voltage with well) same	USPAT;	2004/06/29
		(first with protective)) and ((low with	US-PGPUB;	15:50
		voltage with well) same (second with	EPO; JPO;	
		protective)) and (@ad<20020222 or	DERWENT	-
		@rlad<20020222)		
-	18	((high with voltage with well) same	USPAT;	2004/06/29
		(first with mask)) and ((low with voltage	US-PGPUB;	16:46
		with well) same (second with mask)) and	EPO; JPO;	
		(@ad<20020222 or @rlad<20020222)	DERWENT	2004/05/20
-	30	((high with voltage with well) same	USPAT;	2004/06/29
	l	(first with oxide)) and ((low with	US-PGPUB;	17:38
	1	voltage with well) same (second with	EPO; JPO;	
		oxide)) and (@ad<20020222 or	DERWENT	
1_	54	<pre>@rlad<20020222) ((high with voltage with implant\$5) same</pre>	USPAT;	2004/06/29
_	34	(first with mask)) and ((low with voltage	US-PGPUB;	16:46
		with implant\$5) same (second with mask))	EPO; JPO;	10.30
		and (@ad<20020222 or @rlad<20020222)	DERWENT	
I _	0	(implant\$5 with high with voltage with	USPAT;	2004/06/29
		well) and ((low with voltage with well)	US-PGPUB;	17:40
		same (remov\$3 with second with portion	EPO; JPO;	
		with first with mask)) and (@ad<20020222	DERWENT	
		or @rlad<20020222)		
_	44	(high with voltage with well) and (low	USPAT;	2004/06/29
		with voltage with well) and (remov\$3 with	US-PGPUB;	18:16
		second with portion with first with mask)	EPO; JPO;	
		and (@ad<20020222 or @rlad<20020222)	DERWENT	
-	867	(438/200.ccls. or 438/279.ccls.) and	USPAT;	2004/06/29
	l	(@ad<20020222 or @rlad<20020222)	US-PGPUB;	18:17
			EPO; JPO;	
	L		DERWENT	

[-	205	((438/200.ccls. or 438/279.ccls.) and	USPAT;	2004/06/29
		(@ad<20020222 or @rlad<20020222)) and	US-PGPUB;	18:17
		(high with voltage) and (low with	EPO; JPO;	10.17
		voltage)	DERWENT	
1	159			1 2004/06/20
-	159	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2004/06/29
İ		(@ad<20020222 or @rlad<20020222)) and	US-PGPUB;	18:18
		(high with voltage) and (low with	EPO; JPO;	
		voltage)) and mask\$3	DERWENT	
-	0	wo200237547	USPAT;	2004/07/12
		•	US-PGPUB;	10:56
			EPO; JPO;	l i
			DERWENT	
_	1	"wo 200237547"	USPAT;	2004/07/12
	_		US-PGPUB;	10:58
			EPO; JPO;	10.00
			DERWENT	
		005447		0004/07/10
-	4	985447.ap.	USPAT;	2004/07/12
			US-PGPUB;	10:58
			EPO; JPO;	
			DERWENT	ľ